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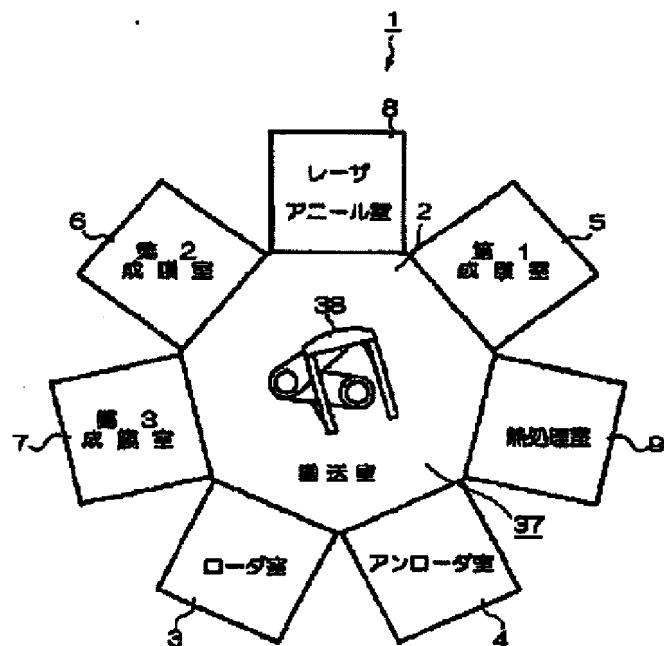
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APPLICANT : FURONTEKKU:KK;

INVENTOR : SAI MOTONARI;

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TITLE : PLASMA CVD DEVICE AND
MANUFACTURE OF
SEMICONDUCTOR DEVICE USING
THE SAME



ABSTRACT : PROBLEM TO BE SOLVED: To provide a plasma CVD device wherein a film-forming process is simplified, suitable, for example, for film-forming a polycrystal silicon film, etc.

SOLUTION: The plasma CVD device comprises a plurality of process chambers comprising three film-forming chambers 5, 6, and 7, a laser anneal chamber 8, and a heat-process chamber 9; a loader chamber 3; an unloader chamber 4; and a transportation chamber 2 provided with a substrate transportation robot for transporting a substrate to be processed among these process chambers. Here, the substrate to be processed is transported among a plurality of process chambers and the transportation chamber 2 without being exposed to an atmosphere. The film-forming chambers 5, 6, and 7 are 2-frequency excitation type plasma film-forming chambers comprising a high-frequency electrode and a susceptor electrode.

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